WHAT IS CLAIMED IS:

1. A blankmask for extreme ultraviolet (EUV) lithography, comprising a substrate, a reflective film formed on the substrate, a capping film formed on the reflective film, and a phase shift film formed on the capping film,

wherein the phase shift film does not include ruthenium (Ru), and comprises:

a first layer formed on the capping film and containing 20 to 50 at% of niobium (Nb), 10 to 40 at% of chrome (Cr), 10 to 60 at% of nitrogen (N), and at least one of oxygen (O)and carbon (C), the first layer having a thickness of 30 to 60 nm and 80% or more of a total thickness of the phase shift film, the first layer having a refractive index (n) of 0.925 to 0.935 and an extinction coefficient (k) of 0.015 to 0.025 with respect to exposure light having a wavelength of 13.5 nm, and

a second layer formed on the first layer and containing one or more of tantalum (Ta) and silicon (Si) in which content of tantalum (Ta) in the second layer is higher than or equal to 50 at%,

wherein the phase shift film is formed directly on the capping film.

2. The blankmask of claim 1, wherein the first layer contains one or more of tantalum (Ta) and silicon (Si).

3. The blankmask of claim 1, wherein the second layer contains one or more of oxygen (O), nitrogen (N), and carbon (C).

4. The blankmask of claim 1, wherein the second layer further contains boron (B).

5. The blankmask of claim 4, wherein content of boron (B) in the second layer ranges from 5 to 20 at%.

6. The blankmask of claim 1, wherein the second layer has a thickness of 2 to 10 nm.

7. The blankmask of claim 1, wherein the second layer has a surface reflectivity of 40% or lower to inspection light having a wavelength of 193 nm.

8. The blankmask of claim 1, wherein the second layer has a refractive index (n) of 0.940 to 0.960 and an extinction coefficient (k) of 0.025 to 0.035 with respect to exposure light having a wavelength of 13.5 nm.

9. The blankmask of claim 1, wherein the phase shift film has a relative reflectivity of 6 to 15% to the reflective film with respect to exposure light having a wavelength of 13.5 nm.

10. A photomask prepared using the blankmask for extreme ultraviolet (EUV) lithography of claim 1.